Toshiba Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1044F

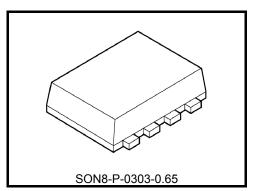
Low-Side Switch for Motor, Solenoid and Lamp Drive

The TPD1044F is a low-side switch.

The IC has a vertical MOSFET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The IC is equipped with intelligent self-protection functions.

Features

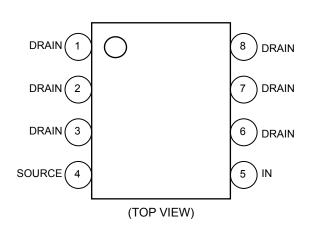
- A monolithic power IC with a new structure combining a control block and a vertical power MOSFET (L^2 - π -MOSV) on single chip.
- Can directly drive a power load from a CMOS or TTL logic.
- Built-in protection circuits against overvoltage (active clamp), overtemperature (thermal shutdown), and overcurrent (current limiter).



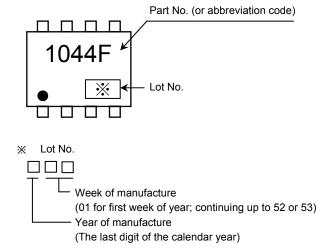
Weight: 0.017 g (typ.)

- Low Drain-Source ON-resistance: RDS (ON) = 0.6Ω (max) (@VIN = 5 V, ID = 0.5 A, Tch = 25° C)
- Low Leakage Current: $IDSS = 10 \mu A (max) (@VIN = 0 V, VDS = 30 V, T_{ch} = 25 °C)$
- Low Input Current: $I_{IN} = 300 \ \mu A (max) (@V_{IN} = 5 \text{ V}, T_{ch} = 25 \text{°C})$
- "PS-8" package with embossed-tape packing.

Pin Assignment (top view)

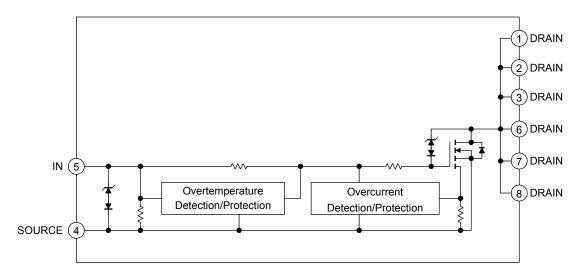


Marking



Note 1: Due to its MOS structure, this product is sensitive to static electricity.

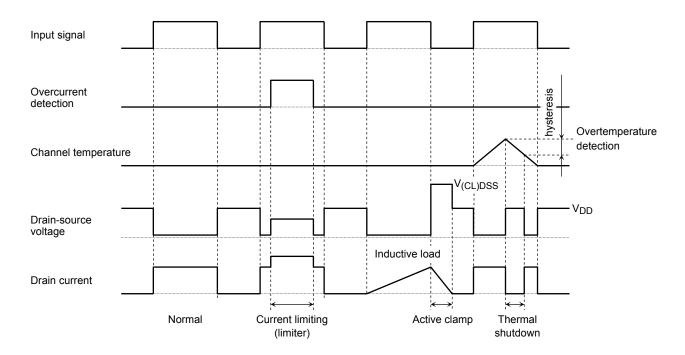
Block Diagram



Pin Description

Pin No.	Symbol	Pin Description			
1,2,3,6,7,8	DRAIN	rain current is limited (by current limiter) if it exceeds 1 A (min) in order to protect the IC.			
4	SOURCE	Source pin.			
5	IN	Input pin. This pin is connected to a pull-down resistor internally, so that even when input wiring is open-circuited, output can never be turned on inadvertently.			

Timing chart



Note 2: The overtemperature detector circuits feature hysteresis. After overtemperature is detected, normal operation is restored only when the channel temperature falls by the hysteresis amount (5°C typ.) in relation to the overtemperature detection temperature.

Truth table

IN	V _{DS}	Output state	Operating state		
L	Н	OFF	Normal		
Н	L	ON	Nomia		
L	Н	OFF	Overcurrent		
Н	Н	current limiting(limiter)	(load short)		
L	Н	OFF	0		
Н	Н	OFF	Overtemperature		



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V _{DS(DC)}	41	V	
Drain current	I _D	Internally Limited	Α	
Input voltage	V _{IN}	-0.3~7	V	
Power dissipation (Note 3)	PD	0.9	W	
Single pulse active clamp capability (Note 4)	E _{AS}	125	mJ	
Active clamp current	I _{AR}	1	Α	
Repetitive active clamp capability (Note 5)	E _{AR}	0.09	mJ	
Operating temperature	T _{opr}	-40~125	°C	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	-55~150	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to ambient	D	138.9	°C/W	
(Note 3)	R _{th (ch-a)}	130.9		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 3:

Drive operation: Mounted on glass epoxy board [25.4mm \times 25.4mm \times 0.8mm]



Note 4: Active clamp capability (single pulse) test condition

 $V_{DD}=40~V,\,T_{ch}=25^{\circ}C(initial),\,L=50~mH,\,I_{AR}=1~A,\,R_{G}=25~\Omega$

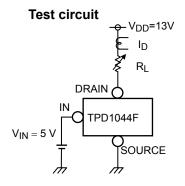
Note 5: Repetitive rating, pulse width limited by maximum channel temperature.

Electrical Characteristics(Ta = 25°C)

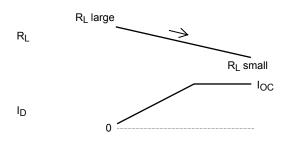
Characteristics	Symbol	Test circuit	Test condition	Min	Тур.	Max	Unit	
Drain-source clamp voltage	V _{(CL) DSS}	-	$V_{IN} = 0 \ V, I_D = 1 \ mA$	41	-	60	V	
Input threshold voltage	V_{th}	-	$V_{DS} = 13 \text{ V}, I_D = 10 \text{ mA}$	1.0	-	2.8	V	
Protective circuit operation input voltage range	V _{IN (opr)}	-	-	3	-	6	V	
Drain cut-off current	I _{DSS}	-	V _{IN} = 0 V,V _{DS} = 30 V	-	-	10	μΑ	
	I _{IH (1)}	-	V _{IN} = 5 V, at normal operation	-	-	300		
Input current	l _{IH} (2)	-	V _{IN} = 5 V, when overcurrent protective circuit is actuated	-	-	350	μΑ	
Drain-source on resistance	R _{DS} (ON)	-	V _{IN} = 5 V, I _D = 0.5 A	-	0.44	0.6	Ω	
Overtemperature detection	T _{OT}	-	V _{IN} = 5 V	150	160	-	°C	
Overcurrent detection	loc	1	V _{IN} = 5 V	1.0	1.8	-	Α	
Switching time	t _{on}	2	$V_{DD} = 13 \text{ V}, V_{IN} = 0 \text{ V/5 V}, I_D = 0.5 \text{ A}$	-	10	-	<i>μ</i> s	
	t _{off}			-	15	-		

Test circuit 1

Overcurrent measuring circuit



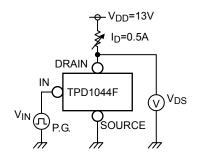
Measured waveforms



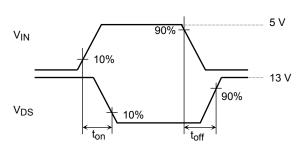
Test circuit 2

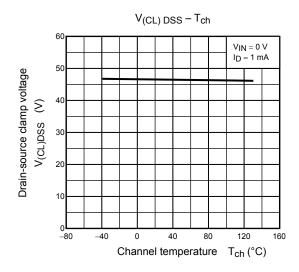
Switching time measuring circuit

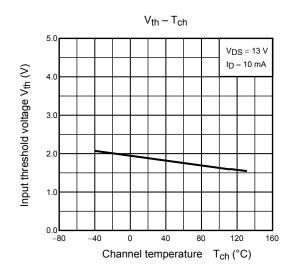
Test circuit

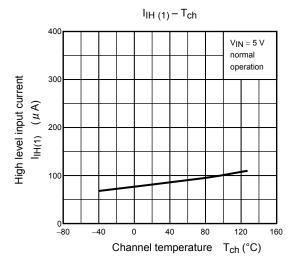


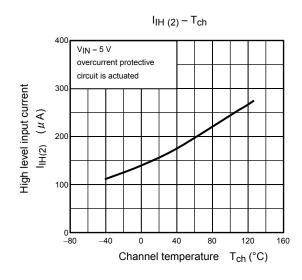
Measured waveforms

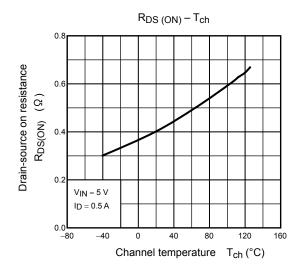


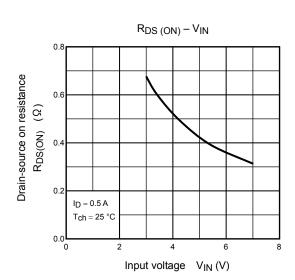


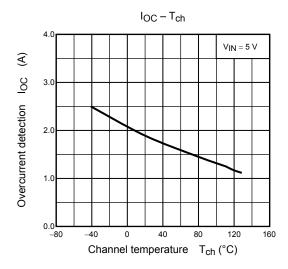


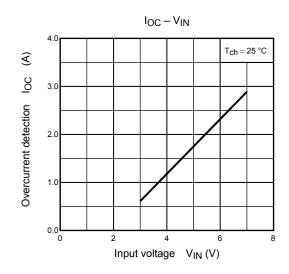


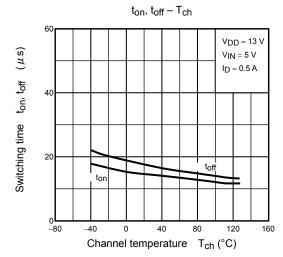


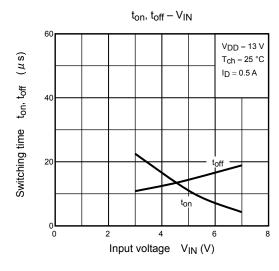


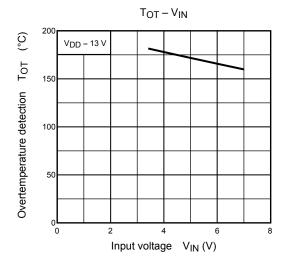


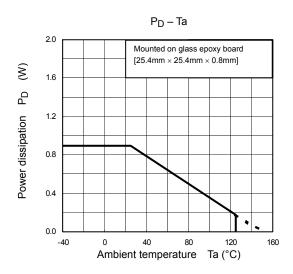


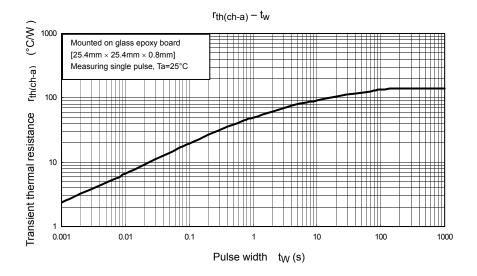




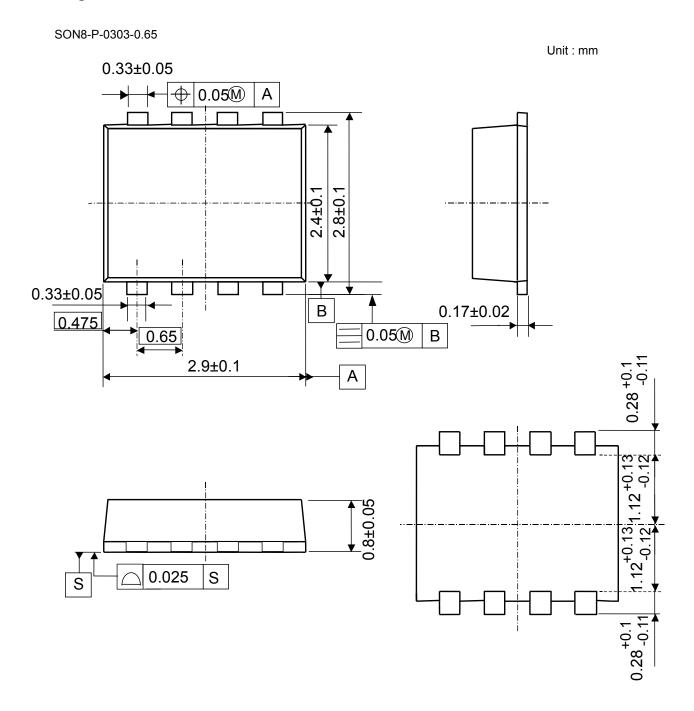








Package Dimensions



Weight: 0.017 g (Typ.)

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20070701-EN GENERAL

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